

# **General Purpose Transistor**

# **NPN Silicon**

# MMBT3904L, SMMBT3904L

#### **Features**

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

#### **MAXIMUM RATINGS**

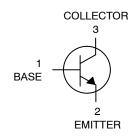
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	200	mAdc
Collector Current - Peak (Note 3)	I <sub>CM</sub>	900	mAdc

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
- 3. Reference SOA curve.





SOT-23 (TO-236) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



1AM = Specific Device Code

M = Date Code\*■ Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT3904LT1G	SOT-23	3000 / Tape &
SMMBT3904LT1G	(Pb-Free)	Reel
MMBT3904LT3G	SOT-23	10,000 / Tape &
SMMBT3904LT3G	(Pb-Free)	Reel

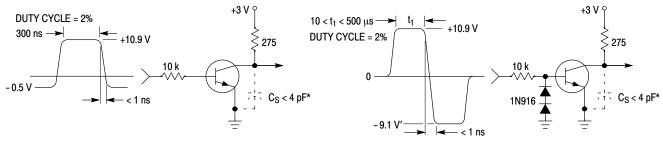
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Chara	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•		
Collector - Emitter Breakdown Voltage (I	V <sub>(BR)CEO</sub>	40	_	Vdc	
Collector – Base Breakdown Voltage (I <sub>C</sub>	= 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	_	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> =	10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	_	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EE</sub>	<sub>3</sub> = 3.0 Vdc)	I <sub>BL</sub>	-	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc,	V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 4)					
$\begin{array}{l} \text{DC Current Gain} \\ \text{(I}_{C} = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \end{array}$		H <sub>FE</sub>	40 70 100 60 30	- 300 - -	-
		V <sub>CE(sat)</sub>	- -	0.2 0.3	Vdc
$\begin{aligned} &\text{Base-Emitter Saturation Voltage} \\ &\text{(I}_{\text{C}} = 10 \text{ mAdc, I}_{\text{B}} = 1.0 \text{ mAdc)} \\ &\text{(I}_{\text{C}} = 50 \text{ mAdc, I}_{\text{B}} = 5.0 \text{ mAdc)} \end{aligned}$		V <sub>BE(sat)</sub>	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS		•	•	•	•
Current - Gain - Bandwidth Product (I <sub>C</sub>	= 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	300	-	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> =	= 0, f = 1.0 MHz)	C <sub>obo</sub>	_	4.0	pF
Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}$ , $I_{C} = 0.5 \text{ Vdc}$	0, f = 1.0 MHz)	C <sub>ibo</sub>	-	8.0	pF
Input Impedance ( $V_{CE} = 10 \text{ Vdc}, I_{C} = 1.0 \text{ Vdc}$	0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0	10	kΩ
Voltage Feedback Ratio ( $V_{CE} = 10 \text{ Vdc}$ ,	$I_C = 1.0 \text{ mAdc, } f = 1.0 \text{ kHz}$	h <sub>re</sub>	0.5	8.0	X 10 <sup>-4</sup>
Small - Signal Current Gain (V <sub>CE</sub> = 10 V	dc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> =	h <sub>oe</sub>	1.0	40	μmhos	
Noise Figure ( $V_{CE}$ = 5.0 Vdc, $I_{C}$ = 100 $\mu$	NF	_	5.0	dB	
SWITCHING CHARACTERISTICS					
Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = -0.5 Vdc,	t <sub>d</sub>	-	35	
Rise Time	I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)	t <sub>r</sub>	-	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc,	t <sub>s</sub>	_	200	
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t <sub>f</sub>	_	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

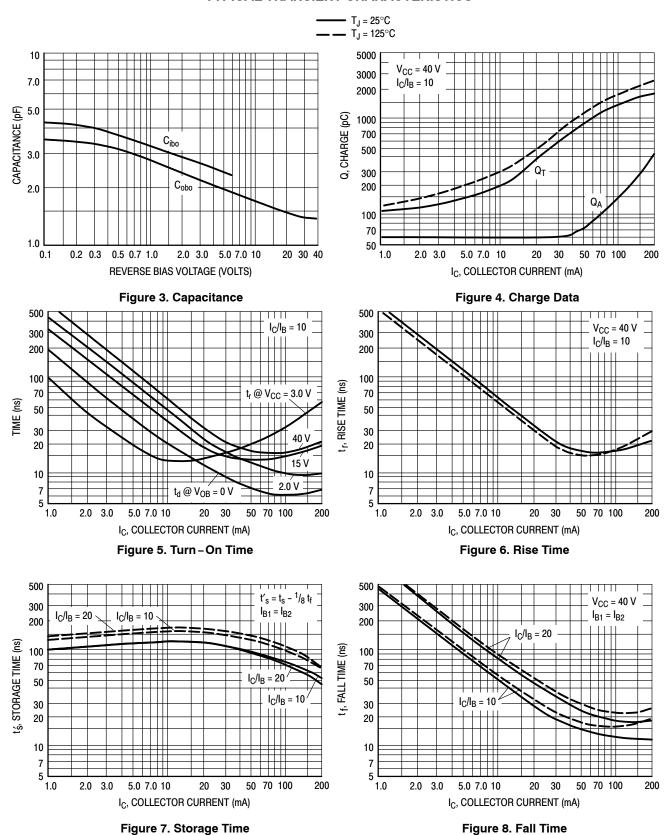


\* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

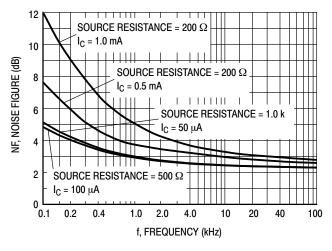
Figure 2. Storage and Fall Time Equivalent Test Circuit

#### TYPICAL TRANSIENT CHARACTERISTICS



# TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS **NOISE FIGURE VARIATIONS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$ 



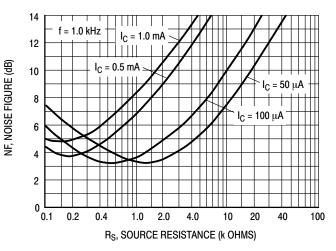
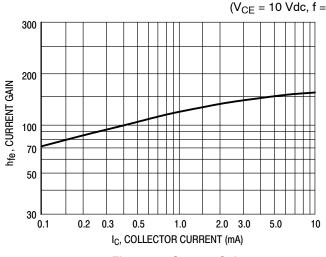


Figure 9.

Figure 10.

#### **h PARAMETERS**



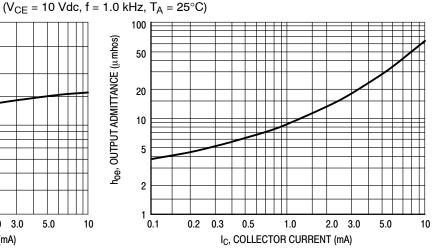
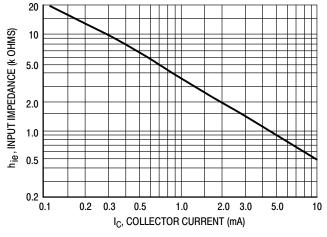
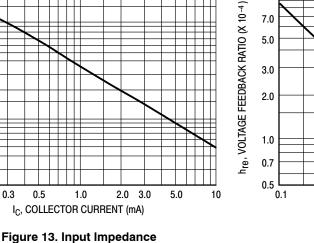


Figure 11. Current Gain

Figure 12. Output Admittance





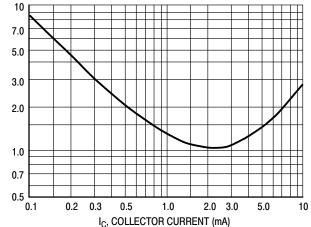


Figure 14. Voltage Feedback Ratio

# **TYPICAL STATIC CHARACTERISTICS**

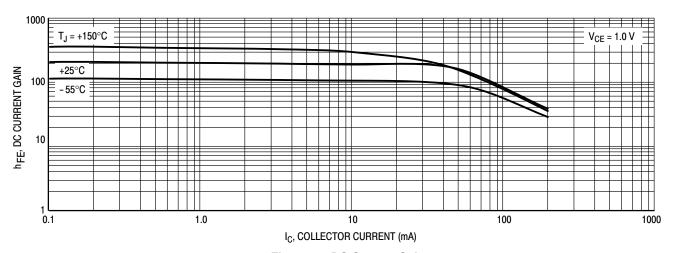


Figure 15. DC Current Gain

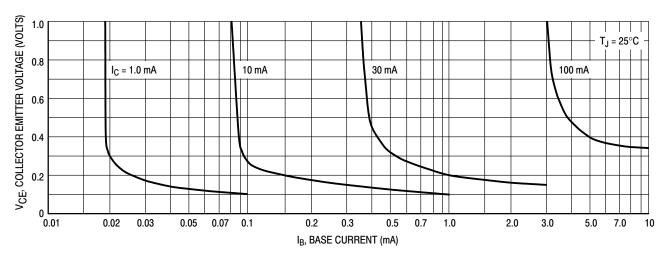


Figure 16. Collector Saturation Region

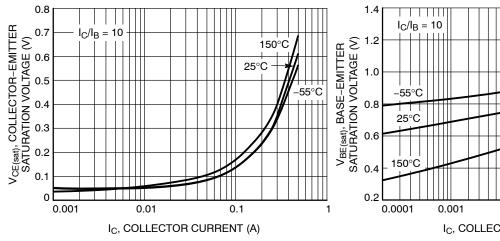


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

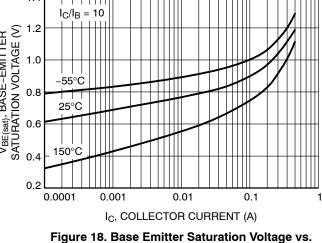


Figure 18. Base Emitter Saturation Voltage vs. Collector Current

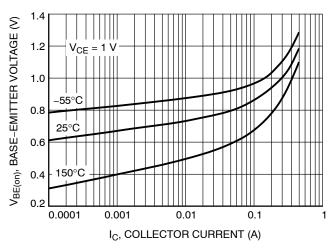


Figure 19. Base Emitter Voltage vs. Collector Current

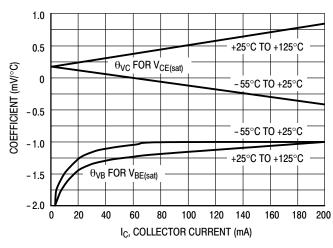


Figure 20. Temperature Coefficients

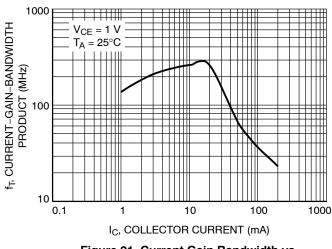


Figure 21. Current Gain Bandwidth vs. Collector Current

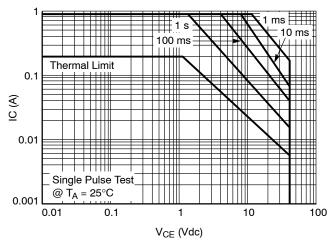


Figure 22. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b **TOP VIEW**







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

3. ANODE

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		10°	O۰		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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